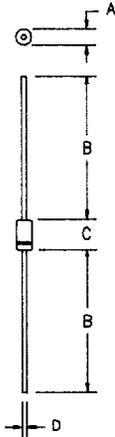


# 5 Amp Schottky Rectifier MS508, MS509, MS510



| Dim. | Inches  |         | Millimeter |         | Notes |
|------|---------|---------|------------|---------|-------|
|      | Minimum | Maximum | Minimum    | Maximum |       |
| A    | .188    | .260    | 4.78       | 6.50    | Dia.  |
| B    | 1.00    | ---     | 25.4       | ---     |       |
| C    | .285    | .375    | 7.24       | 9.52    |       |
| D    | .046    | .056    | 1.17       | 1.42    | Dia.  |

PLASTIC D0201AD

| Microsemi Catalog Number | Working Peak Reverse Voltage | Repetitive Peak Reverse Voltage |   |
|--------------------------|------------------------------|---------------------------------|---|
| MS508                    | 80V                          | 80V                             | <ul style="list-style-type: none"> <li>• Schottky Barrier Rectifier</li> <li>• Guard Ring Protection</li> <li>• Low power loss, high efficiency</li> <li>• High surge capacity</li> <li>• <math>V_{RRM}</math> 80 to 100 Volts</li> </ul> |
| MS509                    | 90V                          | 90V                             |   |
| MS510                    | 100V                         | 100V                            |   |

| Electrical Characteristics   |                             |   |
|------------------------------|-----------------------------|---|
| Average forward current      | I <sub>F(AV)</sub> 5.0 Amps | T <sub>A</sub> = 131°C Square wave, R <sub>θJL</sub> = 11°C/W, L = 1/8"   |
| Average forward current      | I <sub>F(AV)</sub> 5.0 Amps | T <sub>A</sub> = 116°C Square wave, R <sub>θJL</sub> = 14.7°C/W, L = 3/8" |
| Maximum surge current        | I <sub>FSM</sub> 300 Amps   | 8.3ms, half sine, T <sub>J</sub> = 175°C                                  |
| Max peak forward voltage     | V <sub>FM</sub> .60 Volts   | I <sub>FM</sub> = 5.0A; T <sub>J</sub> = 175°C*                           |
| Max peak forward voltage     | V <sub>FM</sub> .80 Volts   | I <sub>FM</sub> = 5.0A; T <sub>J</sub> = 25°C*                            |
| Max peak reverse current     | I <sub>RM</sub> 250 μA      | V <sub>RRM</sub> , T <sub>J</sub> = 25°C                                  |
| Typical junction capacitance | C <sub>J</sub> 280 pF       | V <sub>R</sub> = 5.0V, T <sub>J</sub> = 25°C                              |

\*Pulse test: Pulse width 300 μsec, Duty cycle 2%

| Thermal and Mechanical Characteristics |                           |                                 |
|--|---------------------------|---------------------------------|
| Storage temperature range              | T <sub>STG</sub>          | -40°C to 175°C                  |
| Operating junction temp range          | T <sub>J</sub>            | -40°C to 175°C                  |
| Maximum thermal resistance             | L = 1/8" R <sub>θJL</sub> | 11°C/W Junction to Lead         |
|  | L = 3/8" R <sub>θJL</sub> | 14.7°C/W Junction to Lead       |
| Weight                                 |                           | .032 ounces (1.0 grams) typical |

**Microsemi Corp.**  
**Colorado**

PH: 303-469-2161  
FAX: 303-466-3775

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# MS508, MS509, MS510

Figure 1  
Typical Forward Characteristics

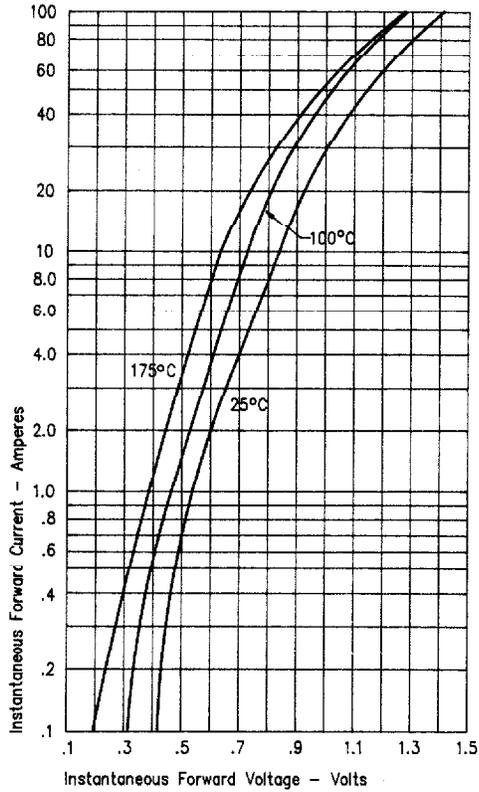


Figure 3  
Typical Junction Capacitance

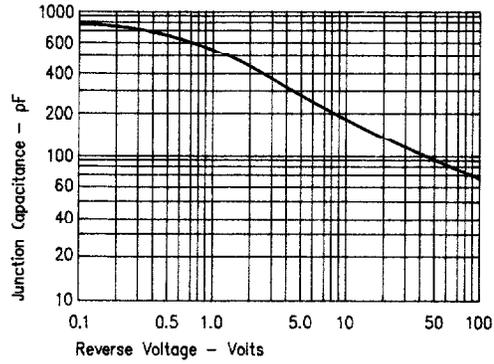


Figure 4  
Forward Current Derating

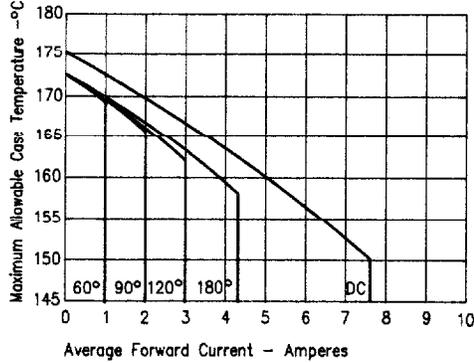


Figure 2  
Typical Reverse Characteristics

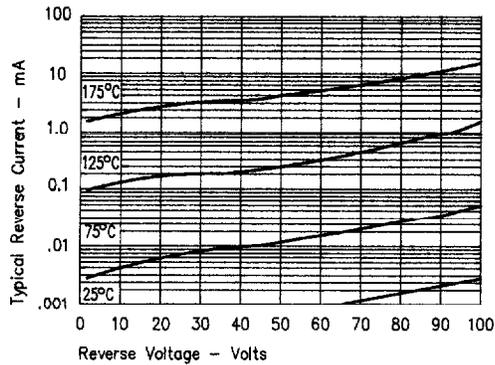


Figure 5  
Maximum Forward Power Dissipation

